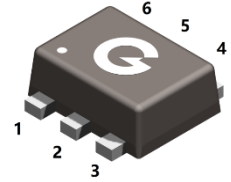
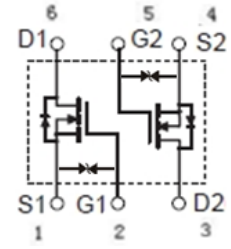


Features

- Advanced planar technology
- Low input capacitance
- High-speed switching
- Drive circuits can be simple
- HBM: JESD22-A114-B: 1C
- RoHS compliant with Halogen-free

HF



SOT-563

Mechanical Data

- Case: SOT-563
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin-Plated Leads, Solderability-per MIL-STD-202, Method 208

Ordering Information

| Part Number | Package | Shipping Quantity | Marking Code |
|-------------|---------|------------------------|--------------|
| BSS3541V | SOT-563 | 3000 pcs / Tape & Reel | 3541 |

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

| Parameter | Symbol | Value | Unit |
|---|------------------|------------|------|
| Drain-Source Voltage | V _{DSS} | 30 | V |
| Gate -Source Voltage | V _{GSS} | ±20 | V |
| Continuous Drain Current (T _A = 25°C) *1 | I _D | 100 | mA |
| Continuous Drain Current (T _A = 70°C) *1 | | 80 | |
| Pulsed Drain Current (t _p = 10μs, T _A = 25°C) | I _{DM} | 400 | mA |
| Power Dissipation (T _A = 25°C) *1 | P _D | 0.15 | W |
| Operating Junction Temperature Range | T _J | -55 ~ +150 | °C |
| Storage Temperature Range | T _{STG} | -55 ~ +150 | °C |

Thermal Characteristics

| Parameter | Symbol | Min. | Typ. | Max. | Unit |
|---------------------------------------|------------------|------|------|------|------|
| Thermal Resistance Junction-to-Air *1 | R _{θJA} | - | - | 833 | °C/W |

Electrical Characteristics (@ T_A = 25°C unless otherwise specified)

| Symbol | Parameter | Test Condition | Min. | Typ. | Max. | Unit |
|---|---------------------------------|--|------|------|------|------|
| Static Characteristics | | | | | | |
| V _{DSS} | Drain-Source Breakdown Voltage | V _{GS} = 0V, I _D = 10μA | 30 | - | - | V |
| I _{DSS} | Drain to Source Leakage Current | V _{DS} = 30V, V _{GS} = 0V | - | - | 1 | μA |
| I _{GSS} | Gate-body Leakage | V _{GS} = ±20V, V _{DS} = 0V | - | - | ±1 | μA |
| On Characteristics | | | | | | |
| R _{DS(ON)} | Drain-Source On-resistance *2 | V _{GS} = 4V, I _D = 10mA | - | 4 | 8 | Ω |
| | | V _{GS} = 2.5V, I _D = 1mA | - | 6 | 13 | |
| V _{GS(TH)} | Gate Threshold Voltage | V _{DS} = 3V, I _D = 100μA | 0.8 | 1.25 | 1.5 | V |
| R _G | Gate Resistance | V _{GS} = 0V, f = 1MHz | - | 288 | - | Ω |
| g _{fs} | Transconductance | V _{DS} = 3V, I _D = 10mA | 20 | - | - | mS |
| Dynamic Characteristics | | | | | | |
| C _{ISS} | Input Capacitance | V _{GS} = 0V V _{DS} = 5V f = 1.0MHz | - | 14 | - | pF |
| C _{OSS} | Output Capacitance | | - | 11 | - | |
| C _{RSS} | Reverse Transfer Capacitance | | - | 5 | - | |
| Switching Characteristics | | | | | | |
| t _{d(on)} | Turn-on Delay Time *3 | V _{DD} = 5V, I _D = 10mA V _{GS} = 5V, R _G = 10Ω R _L = 500Ω | - | 15 | - | ns |
| t _r | Turn-on Rise Time *3 | | - | 35 | - | |
| t _{d(off)} | Turn-Off Delay Time *3 | | - | 80 | - | |
| t _f | Turn-Off Fall Time *3 | | - | 80 | - | |
| Source-Drain Diode Characteristics | | | | | | |
| V _{SD} | Diode Forward Voltage *2 | I _{SD} = 10mA, V _{GS} = 0V | - | 0.7 | 1.2 | V |

Notes:

1. The data tested by surface mounted on a minimum recommended FR-4 board
2. The data tested by pulsed, pulse width ≤ 300μs, duty cycle ≤ 2%
3. Guaranteed by design, not subject to production

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

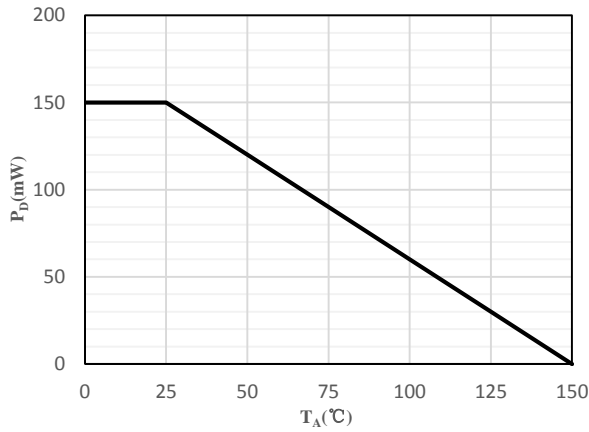


Fig 1 Power Dissipation

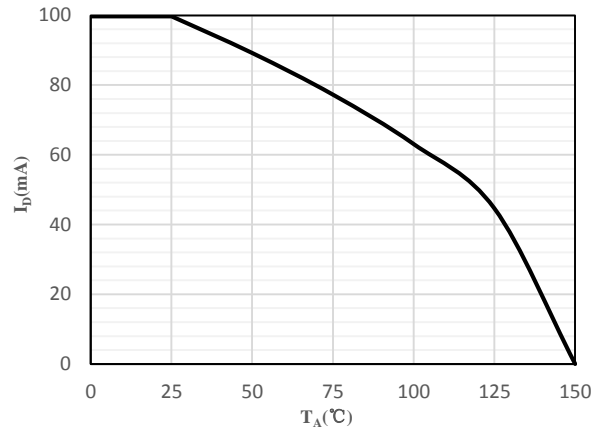


Fig 2 Drain Current

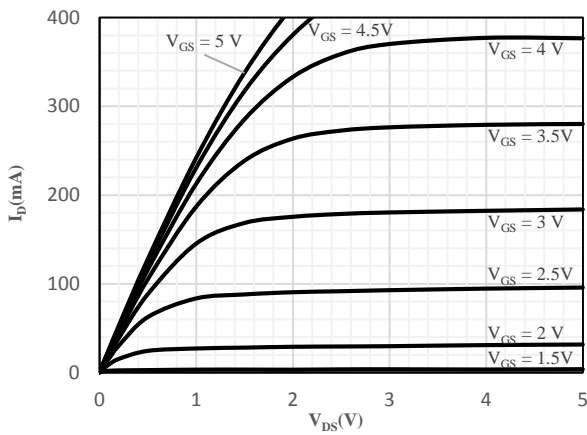


Fig 3 Typical Output Characteristics

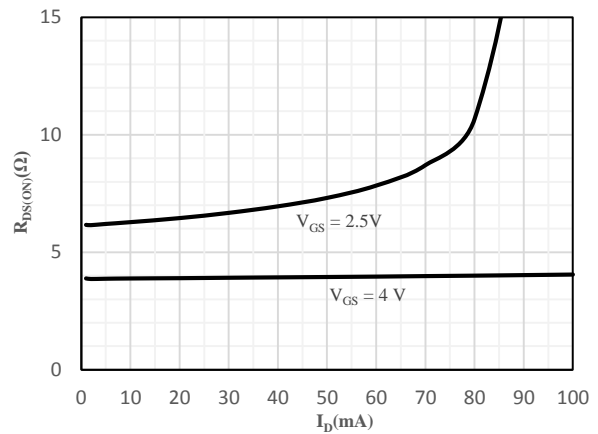


Fig 4 On-Resistance vs. Drain Current and Gate Voltage

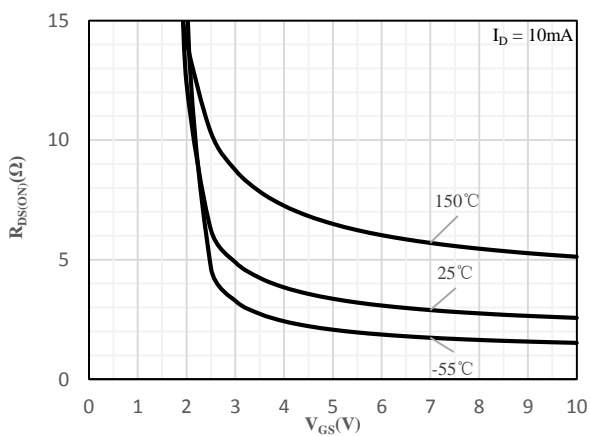


Fig 5 On-Resistance vs. Gate-Source Voltage

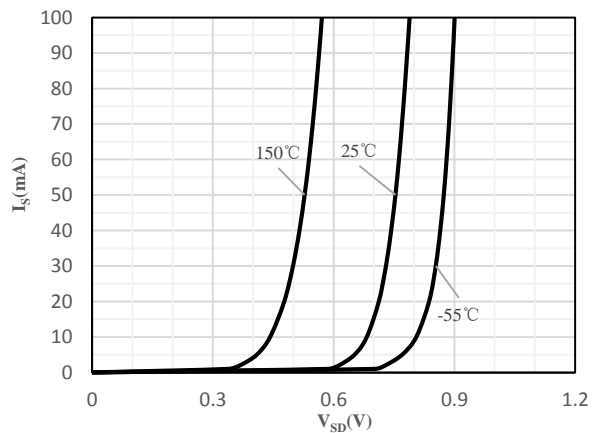


Fig 6 Body-Diode Characteristics

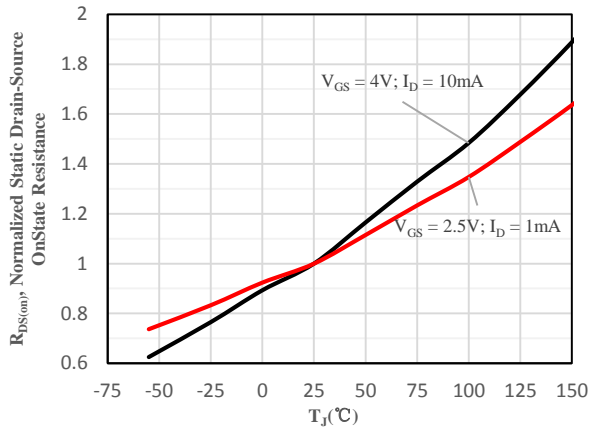


Fig 7 Normalized On-Resistance vs. Junction Temperature

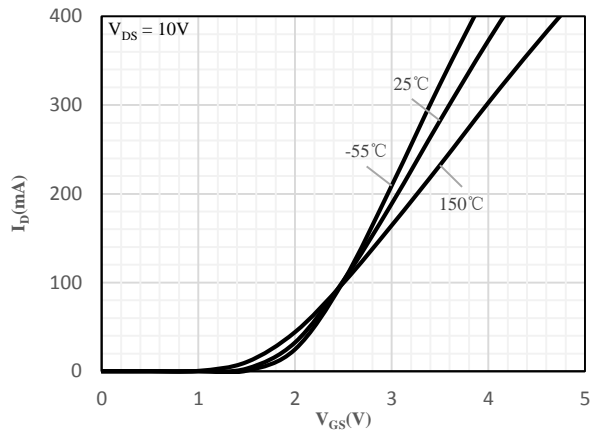


Fig 8 Transfer Characteristics

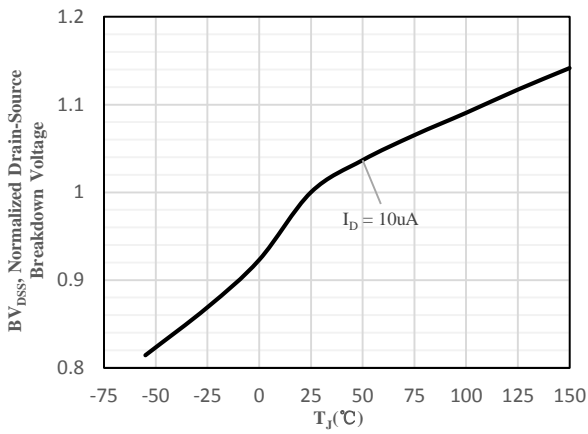


Fig 9 Normalized Breakdown Voltage vs. Junction Temperature

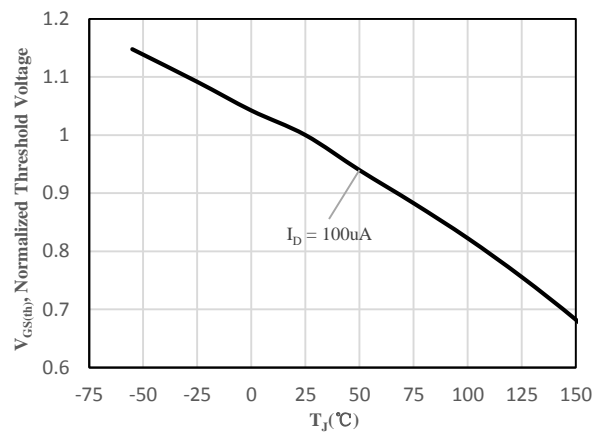


Fig 10 Normalized $V_{GS(th)}$ vs. Junction Temperature

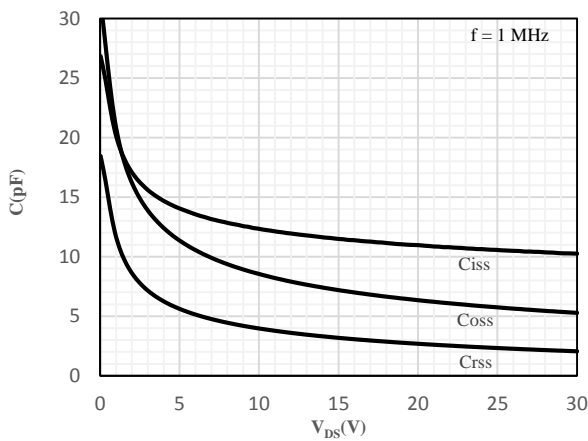


Fig 11 Capacitance Characteristics

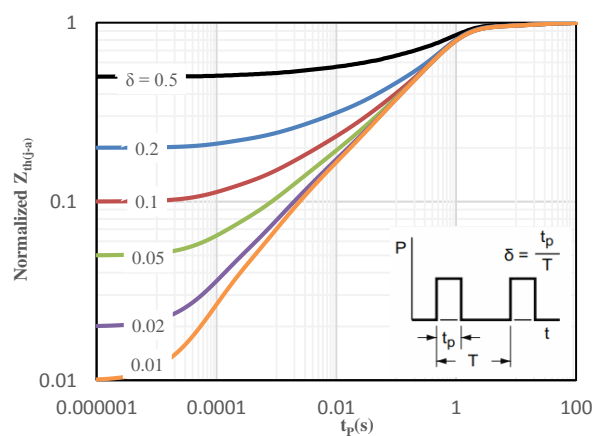
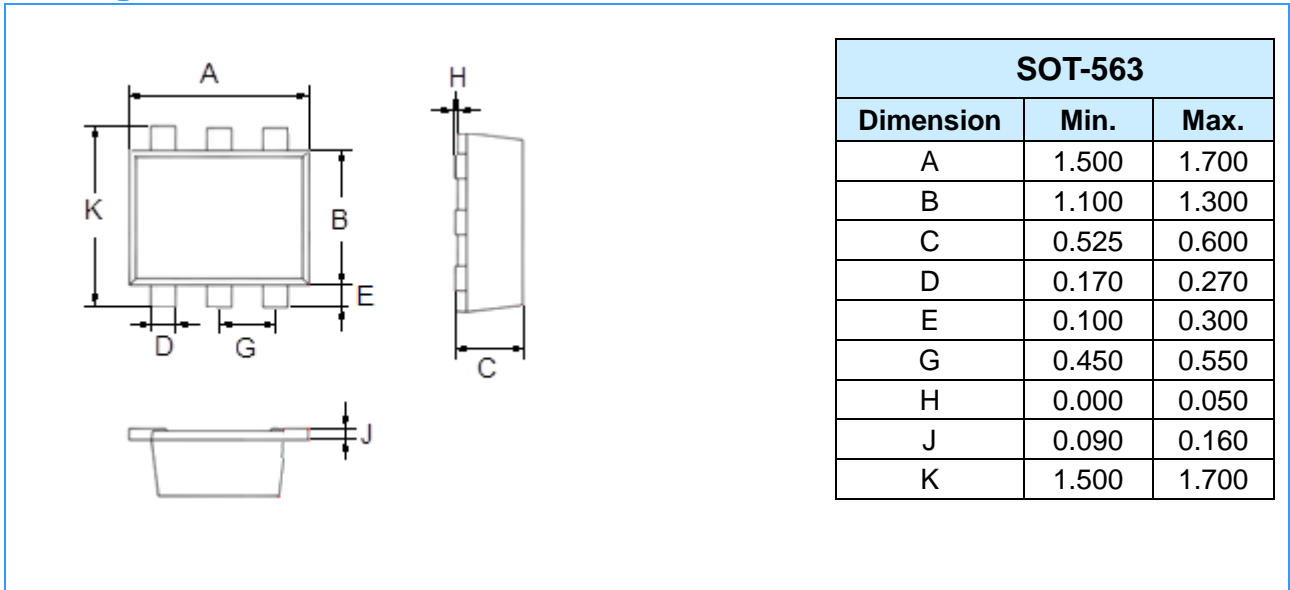


Fig 12 Normalized Maximum transient thermal impedance

Package Outline Dimensions (Unit: mm)



Mounting Pad Layout (Unit: mm)

